JANHCF1N5802, JANHCF1N5804, JANHCF1N5806 JANKCF1N5802, JANKCF1N5804, JANKCF1N5806

ULTRAFAST RECOVERY SILICON RECTIFIER DIE

TECHNICAL DATA DATA SHEET 5498, REV -

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FEATURES / BENEFITS:

- ✓ Die fabricated on a MIL-PRF-19500 JANKC qualified manufacturing line
- ✓ Class H and class K element evaluation per MIL-PRF-19500/477
- ✓ All ratings are @ T_A = 25 °C unless otherwise specified

ELECTRICAL CHARACTERISTICS:

Maximum Ratings:

| Characteristics | Symbol | Condition | Min. | Max. | Units |
|------------------------------|-------------|--------------------------|------|------|-------|
| Peak Inverse Voltage | | | | | |
| DC Blocking Voltage | V_{RWM} | | | | |
| JANK(H)CF1N5802 | V_R | _ | | 50 | V |
| JANK(H)CF1N5804 | | _ | | 100 | v |
| JANK(H)CF1N5806 | | | | 150 | |
| Breakdown Voltage | | | | | |
| JANK(H)CF1N5802 | V_{BR1} | @ I _{BR} =100uA | 60 | | |
| JANK(H)CF1N5804 | V BR1 | ₩ IBR=100uA | 110 | | V |
| JANK(H)CF1N5806 | | | 160 | | |
| Max. Average Forward Current | $I_{F(AV)}$ | @ 55°C | | 1.0 | Α |
| Max. Peak One Cycle Non- | I_{FSM} | 8.3 ms, sine pulse (1) | | 35 | Α |
| Repetitive Surge Current | | 0.5 ms, sine puise | | | |
| Max. Junction Temperature | T_J | - | -55 | +175 | °C |
| Max. Storage Temperature | T_{stg} | - | -55 | +175 | °C |

⁽¹⁾ Tested in SHD package

Electrical Characteristics:

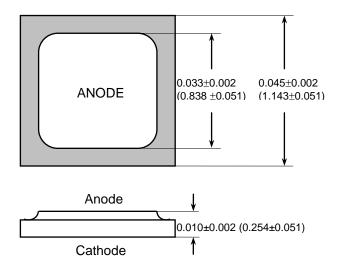
| Characteristics | Symbol | Condition | Max. | Units |
|--|-----------------|---|------------------|-------|
| Max. Forward Voltage Drop | V_{F1} | 1A, pulse, T _J = 25 °C | 0.875 | V |
| | V_{F2} | 2.5A, pulse, T _J = 25 °C | 0.975 | V |
| | V_{F3} | 1A, pulse, T _J = 125 °C | 0.800 | V |
| | V_{F4} | 1A, pulse, T _J = -55 °C | 1.075 | V |
| Max. Reverse Current | I _{R1} | $V_R = V_{RWM}$, pulse, $T_J = 25$ °C | 1.0 | μА |
| | I _{R2} | $V_R = V_{RWM}$, pulse, $T_J = 125 ^{\circ}C$ | 175 | μΑ |
| Breakdown Voltage JANK(H)CF1N5802 JANK(H)CF1N5804 JANK(H)CF1N5806 | V_{BR2} | @ I _{BR} =100uA, T _J = -55 °C | 50 100 150 | V |
| Reverse Recovery Time | t _{rr} | $I_F = I_R = 0.5A$, $I_{RM} = 0.05A$ | 25 | ns |
| Max. Junction Capacitance | Ст | $V_R = 10V$, $T_C = 25$ °C $f_{SIG} = 1MHz$, $V_{SIG} = 50mV$ (p-p) | 25 | pF |

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PACKAGE DIMENSIONS (inches/mm):



Top anode and bottom cathode

Top Metal Ti (0.3 kA) / Al (34 kA minimum) Bottom Metal Ti (1.2 kA) / Ni (1.8 kA) / Au (3.6 kA minimum)

PART ORDERING INFORMATION:



| Suffix | Part Number | Description |
|--------|-------------|---------------|
| Н | JANHCF5806 | Class H Level |
| K | JANKCF5806 | Class K Level |

SENSITRON SEMICONDUCTOR

JANHCF1N5802, JANHCF1N5804, JANHCF1N5806 JANKCF1N5802, JANKCF1N5804, JANKCF1N5806

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